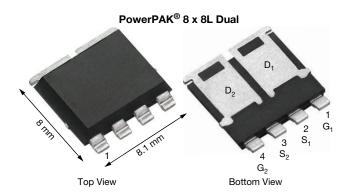


Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0023			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0027			
I _D (A) per leg	100			
Configuration	Dual			
Package	PowerPAK 8 x 8L			

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Fully lead (Pb)-free device
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







G ₁ O S ₁	G_2 G_2 G_2
N-Channel MOSFET	N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40	V
Gate-source voltage		V_{GS}	± 20	V
Continuous drain current	$T_C = 25 ^{\circ}C^{a}$	1	100	
Continuous drain current	T _C = 125 °C	I _D	78	
Continuous source current (diode conduction	I _S	68	Α	
Pulsed drain current ^b	I _{DM}	400		
Single pulse avalanche current L = 0.1 mH		I _{AS}	45	1
Single pulse avalanche energy	L = U.1 IIII	E _{AS}	103	mJ
Maximum power dissipation ^b	T _C = 25 °C	D	75	W
maximum power dissipation ⁵	T _C = 125 °C	P_{D}	25	VV
Operating junction and storage temperature	T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e		-	260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	60	°C/W
Junction-to-case (drain)		R_{thJC}	2	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 20 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	40	-	-	Α
		V _{GS} = 10 V	I _D = 5 A	-	0.0018	0.0023	
Drain acurae en etata registance à	В	V _{GS} = 4.5 V	I _D = 5 A	-	0.0023	0.0027	Ω
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 5 A, T _J = 125 °C	-	-	0.0035	52
		V _{GS} = 10 V	I _D = 5 A, T _J = 175 °C	-	-	0.0040	
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 15 A		-	120	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	5210	7300	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	1530	2145	pF
Reverse transfer capacitance	C _{rss}			-	140	200	
Total gate charge ^c	Qg			-	98	45	
Gate-source charge c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 10 \text{ A}$	-	16	-	nC
Gate-drain charge ^c	Q_{gd}			-	17	-	
Gate resistance	R _g		f = 1 MHz	0.7	1.6	2.6	Ω
Turn-on delay time ^c	t _{d(on)}			-	15	21	
Rise time ^c	t _r	V _{DD} =	20 V, R_L = 1.3 Ω,	-	16	23	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 15 A$,	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	50	70	ns
Fall time ^c	t _f			-	14	20	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed current ^a	I _{SM}			-	-	272	Α
Forward voltage	V _{SD}	I _F =	40 A, V _{GS} = 0 V	-	1	1.2	V
Body diode reverse recovery time	t _{rr}			-	57	80	ns
Body diode reverse recovery charge	Q _{rr}	1	A -1:/-1+ 100 A/	-	61	86	nC
Reverse recovery fall time	ta	$I_F = 40$	A, di/dt = 100 A/μs	-	26	36	
Reverse recovery rise time	t _b	7		-	31	43	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	1.85	2.6	Α

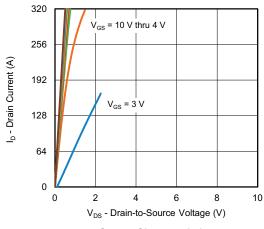
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

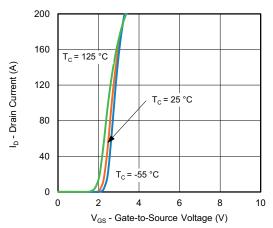
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



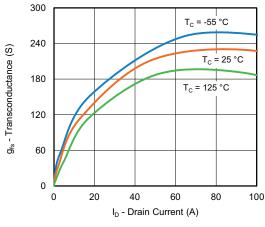
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



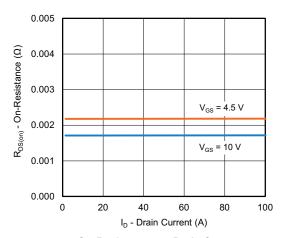
Output Characteristics



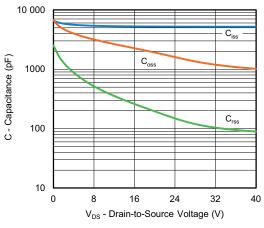
Transfer Characteristics



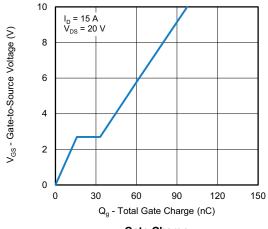
Transconductance



On-Resistance vs. Drain Current



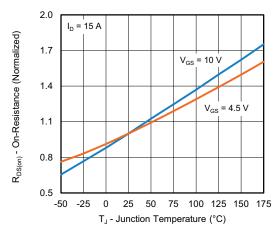
Capacitance



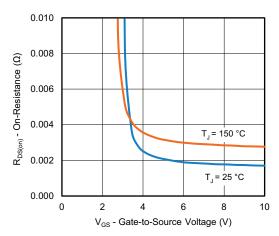
Gate Charge



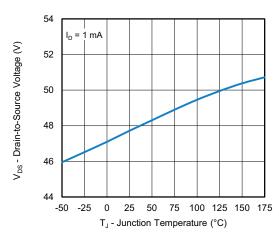
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



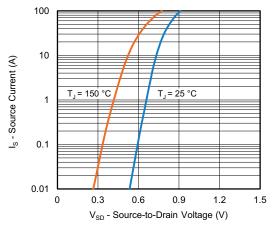
On-Resistance vs. Gate-to Source Voltage



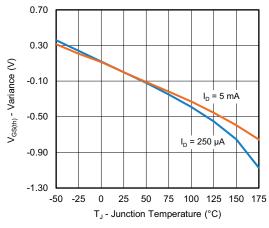
Drain Source Breakdown vs. Junction Temperature

Note

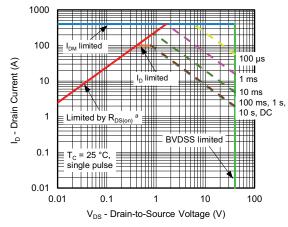
a. $V_{GS} > minimum \ V_{GS}$ at which $R_{DS(on)}$ is specified



Source Drain Diode Forward Voltage

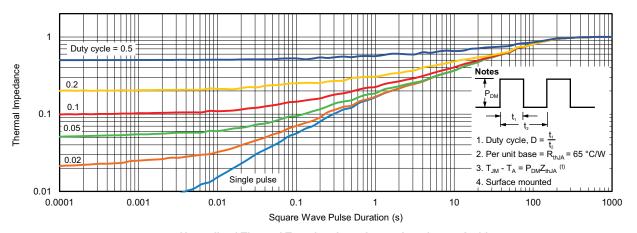


Threshold Voltage

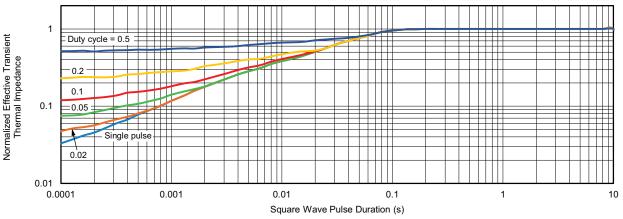


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

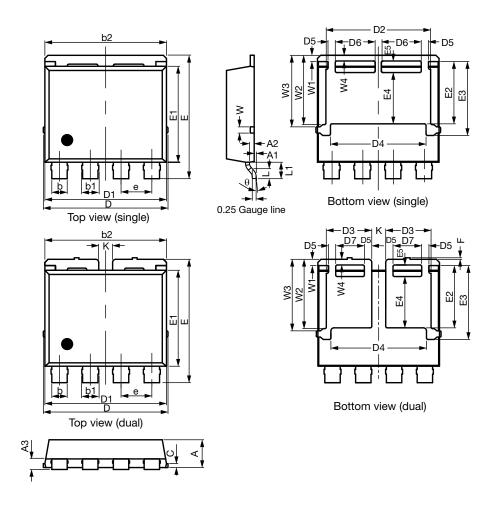
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg277854.



PowerPAK® 8 x 8L Case Outline



DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.70	1.80	1.90	0.067	0.071	0.075		
A1	0.00	0.08	0.13	0.000	0.003	0.005		
A2	0.25	0.30	0.35	0.010	0.012	0.014		
A3	0.55	0.62	0.70	0.022	0.024	0.028		
b	0.92	1.00	1.08	0.036	0.039	0.043		
b1	1.02	1.10	1.18	0.040	0.043	0.046		
b2	7.80	7.90	8.00	0.307	0.311	0.315		
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	8.00	8.10	8.25	0.315	0.319	0.325		
D1	7.80	7.90	8.00	0.307	0.311	0.315		
D2	6.70	6.80	6.90	0.264	0.268	0.272		
D3	2.85	2.95	3.05	0.112	0.116	0.120		
D4	6.11	6.21	6.31	0.241	0.244	0.248		
D5	0.37	0.47	0.57	0.015	0.019	0.022		
D6	2.49	2.59	2.69	0.098	0.102	0.106		
D7	1.76	1.86	1.96	0.069	0.073	0.077		

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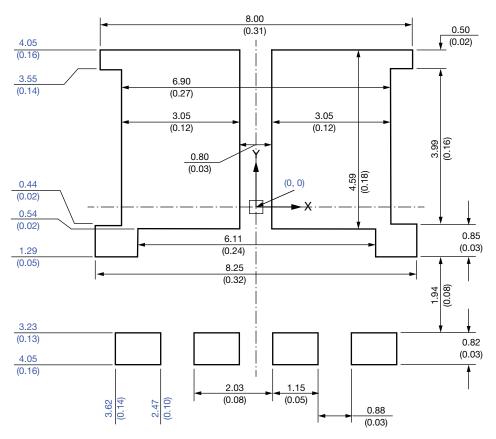
D114	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
е	1.95	2.00	2.05	0.077	0.079	0.081	
E	7.90	8.00	8.10	0.311	0.315	0.319	
E1	6.12	6.22	6.32	0.241	0.245	0.249	
E2	3.94	4.04	4.14	0.140	0.159	0.163	
E3	4.69	4.79	4.89	0.185	0.189	0.193	
E4	3.23	3.33	3.43	0.127	0.131	0.135	
E5	0.65	0.75	0.85	0.026	0.030	0.033	
F	0.00	0.10	0.15	0.000	0.004	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K	0.80	0.90	1.00	0.031	0.035	0.039	
W	0.30	0.40	0.50	0.012	0.016	0.020	
W1	0.30	0.40	0.50	0.012	0.016	0.020	
W2	4.39	4.49	4.59	0.173	0.177	0.181	
W3	4.54	4.64	4.74	0.179	0.183	0.187	
W4	0.32	0.37	0.42	0.013	0.015	0.017	
θ	6°	10°	14°	6°	10°	14°	

C17-1388-Rev. B, 16-Oct-17

DWG: 6026



Recommended Minimum PADs for PowerPAK® 8 x 8L Dual



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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